


REMARKS

The attached Appendix includes marked-up copies of each rewritten paragraph (37 C.F.R. §1.121(b)(1)(iii)).

Respectfully submitted,


James A. Oliff
Registration No. 27,075

Joel S. Armstrong
Registration No. 36,430

JAO:JSA/cln

Date: June 27, 2001

OLIFF & BERRIDGE, PLC
P.O. Box 19928
Alexandria, Virginia 22320
Telephone: (703) 836-6400

DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461
--

APPENDIX

Changes to Specification:

Page 23, lines 6-17:

Next, when the working reticle WR is illuminated by the illumination optical system 31 and the reduced image of this pattern is transferred onto the wafer W through the projection optical system 33 as shown in Fig. 4, deformation of some extent of the projected image by the optical proximity effect, and by extension deformation of a pattern to be formed are generated. Especially when a pattern to be transferred is a fine dense pattern, there is an adverse possibility that the deformation amount exceeds a predetermined tolerance. Thereupon, in this example, the influence of the optical proximity effect is corrected as will be explained with reference to ~~Fig. 2~~ Figs. 2A, 2B1, 2B2, 2C1 and 2C2.